Thin film filter STBP200-4R2-M514

COM-MW TECHNOLOGY

Bandwidth17.9-22.1GHz, Rejection40@DC-16.0GHz, 40@24.5-45.0GHz

Product features

High precision machining technology

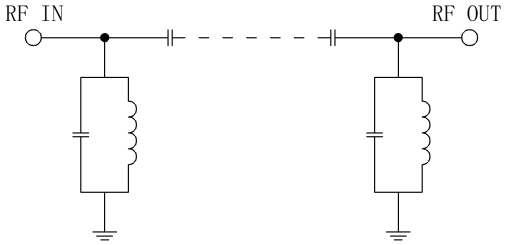
Low temperature drift, high power.

Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

Reference picture

Schematic diagram



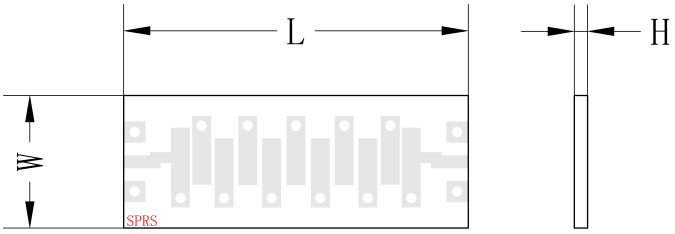
Tech specifications

Items	Parameters	Units
Center Frequency	20.0	GHz
Bandwidth	17.9-22.1	GHz
Center loss	1.5	dB
Ripple	1.0	dB
VSWR	1.7:1	
Group delay ripple	0.4	ns
Rejection	40@DC-16.0GHz	dBc
Rejection	40@24.5-45.0GHz	dBc

Other requirement (Design assurance)

power	2W CW
Operation Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:6.0，W:2.5，h:0.26

Outline drawing: Port centered



Note: The specifications and performance data contained in this data sheet are based on tests established by CMW.

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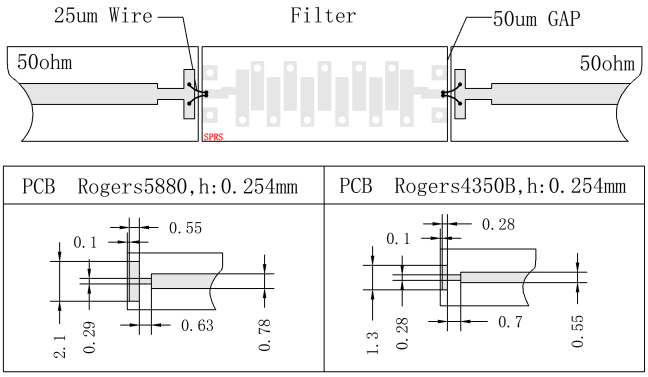
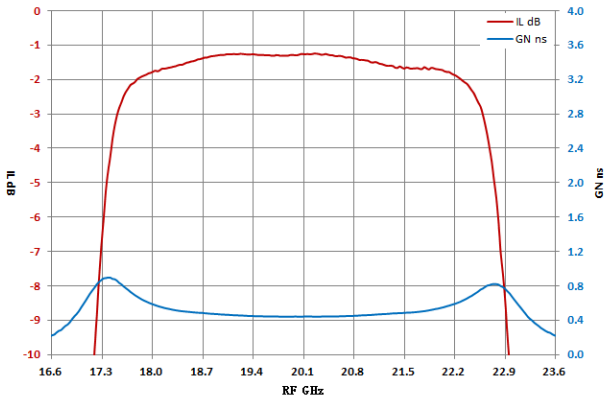
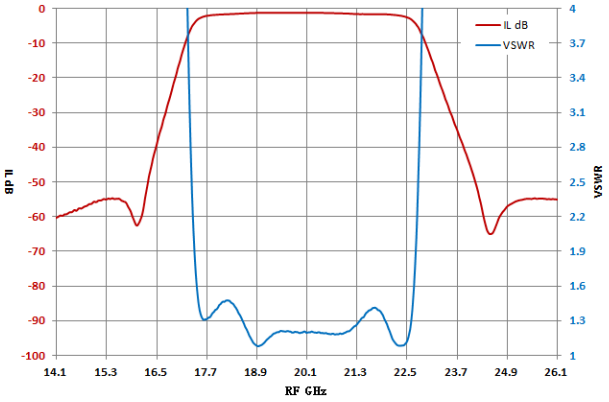
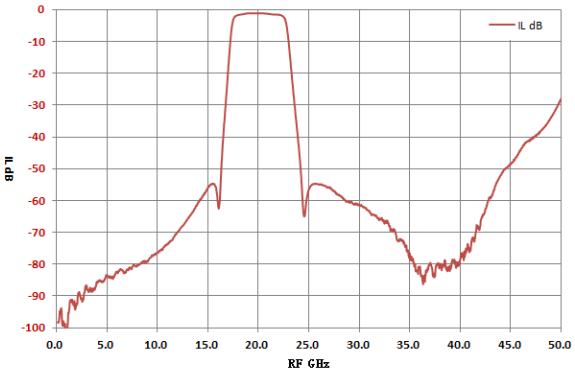
Suggested PCB Layout



Typical test curve







Note

1: The chip is recommended to be used in separate chambers, with one side 0.1mm away from the side wall and the surface 1.74mm away from the top cover. The ports are interchangeable;

2: Suggest using conductive adhesive for bonding;

3:芯片应安装在可伐(推荐) 或铜等与陶瓷热膨胀系数(6.7ppm/C)相近的材料，载体厚度≥0.2mm;

4: Suggest using a T-shaped structure for microstrip bonding.

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